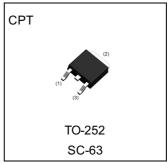


PNP -2.0A -80V Middle Power Transistor

Parameter	Value
V _{CEO}	-80V
I _C	-2A

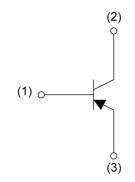
Outline



Features

- 1) Suitable for Middle Power Driver.
- 2) Complementary NPN Types: 2SCR574D.
- 3) Low $V_{CE(sat)}$ $V_{CE(sat)}$ =-400mV(Max.). (I_C/I_B =-1A/-50mA)

•Inner circuit



- (1) Base
- (2) Collector
- (3) Emitter

Application

LOW FREQUENCY AMPLIFIER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SAR574D	CPT	6595	TL	330	16	2500	AR574

● Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V _{CEO}	-80	V
Emitter-base voltage	V _{EBO}	-6	V
Calle store at inner at	I _C	-2	Α
Collector current	I _{CP} *1	-4	Α
Base current	I _B	-0.5	Α
Power dissipation	P _D *2	10	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = -100μA	-80	-	1	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-80	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = -100μA	-6	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -80V	-	-	-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	-	-	-1	μA
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -1A$, $I_B = -50mA$	-	-200	-400	mV
DC current gain	h _{FE}	$V_{CE} = -3V, I_{C} = -100 \text{mA}$	120	-	390	-
Transition frequency	f _T *3	$V_{CE} = -10V, I_{E} = 500 \text{mA},$ f = 100MHz	-	280	-	MHz
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0A, f = 1MHz	-	30	-	pF
Turn-On time	t _{on}	I _C = -1A, I _{B1} = -100mA,	1	50	1	ns
Storage time	t _{stg}	I _{B2} = 100mA, V _{CC} ≃ -10V,	1	300	-	ns
Fall time	t _f	$R_L = 10\Omega$ See test circuit	-	100	-	ns

^{*1} Pw=10ms Single Pulse

^{*2} Tc=25℃

^{*3} PULSED

● Electrical characteristic curves(T_a = 25°C)

Fig.1 Grounded Emitter Propagation Characteristics

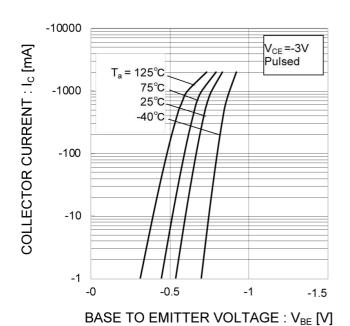
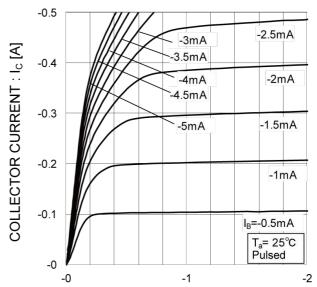


Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

Fig.3 DC Current Gain vs. Collector Current(I)

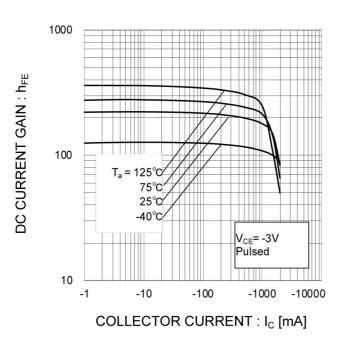
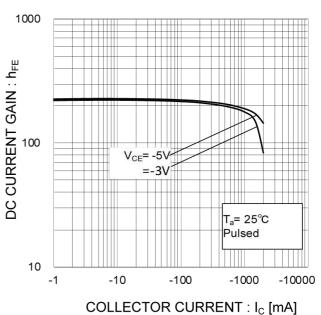


Fig.4 DC Current Gain vs. Collector Current(II)



● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(I)

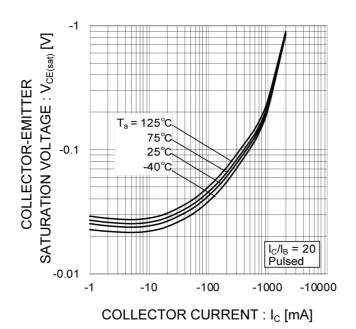


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current(II)

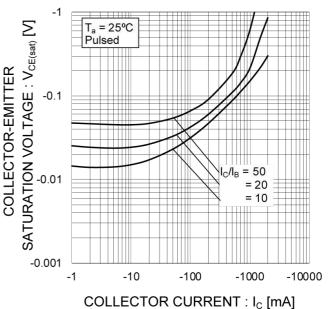


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

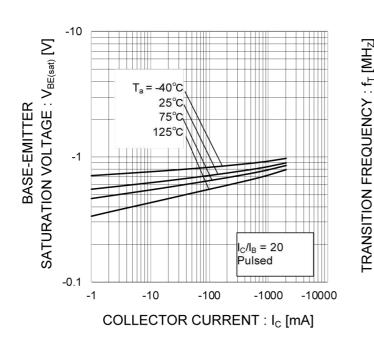
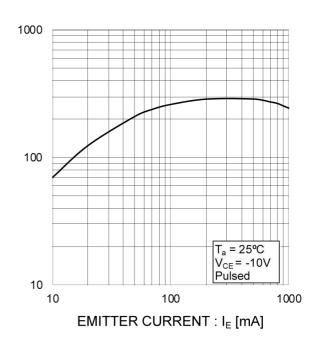


Fig.8 Gain Bandwidth Product vs. Emitter Current



● Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter input capacitance vs. **Emitter-Base Voltage** Collector output capacitance vs. Collector-Base Voltage

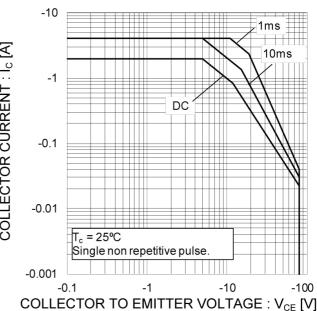
COLLECTOR OUTPUT CAPACITANCE : C_{ob} [pF] EMITTER INPUT CAPACITANCE : C_{ib} [pF] -10 COLLECTOR CURRENT : I_C [A] C_{ib} -1 -0.1 T_a = 25℃ -0.01 = 1MHz

-0.1 COLLECTOR-BASE VOLTAGE : V_{CB} [V] EMITTER-BASE VOLTAGE : V_{EB} [V]

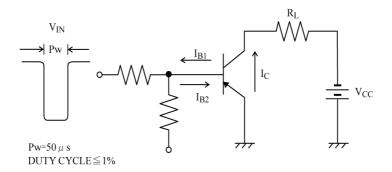
 $I_E = 0A$

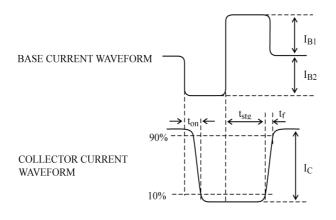
= 0A

Fig.10 Safe Operating Area



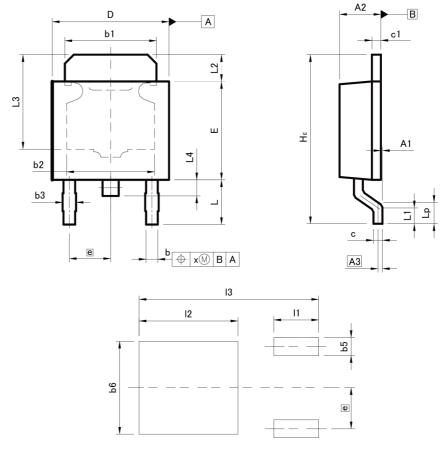
SWITCHING TIME TEST CIRCUIT





Dimensions

CPT



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.15	0.000	0.006	
A2	2.20	2.50	0.087	0.098	
A3	0.:	25	0.010		
b	0.55	0.75	0.022	0.030	
b1	5.00	5.30	0.197	0.209	
b2	5.	00	0.197		
b3	0.	75	0.030		
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.30	6.70	0.248	0.264	
Е	5.40	5.80	5.80 0.213		
е	2.30		0.0	91	
HE	9.00	10.00	0.354	0.394	
L	2.20	2.80	0.087	0.110	
L1	0.80	1.40	0.031	0.055	
L2	1.20	1.80	0.047	0.071	
L3	5.30		0.209		
L4	0.90		0.035		
Lp	1.00	1.60	0.039	0.063	
Х	_	0.25	_	0.010	

DIM	MILIM	ETERS	INCHES		
	MIN	MAX	MIN	MAX	
b5	_	1.00	-	0.04	
b6	-	5.20	-	0.205	
l1	_	2.50	-	0.098	
12	_	5.50	_	0.217	
13	_	10.00	_	0.394	

Dimension in mm/inches



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